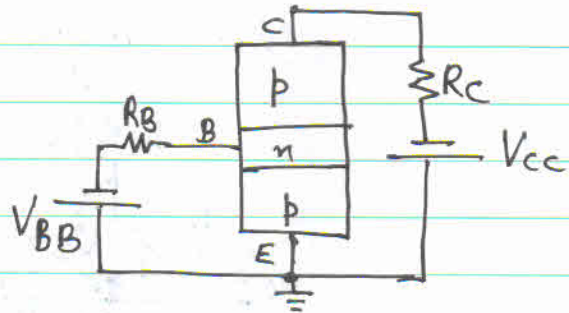
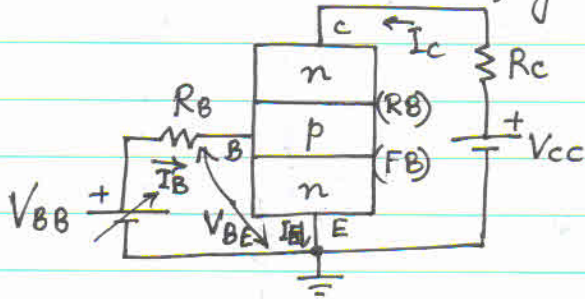


→ Common Emitter Configuration:



Common emitter current gain: $\beta = \frac{i_c}{i_B} \gg 1$

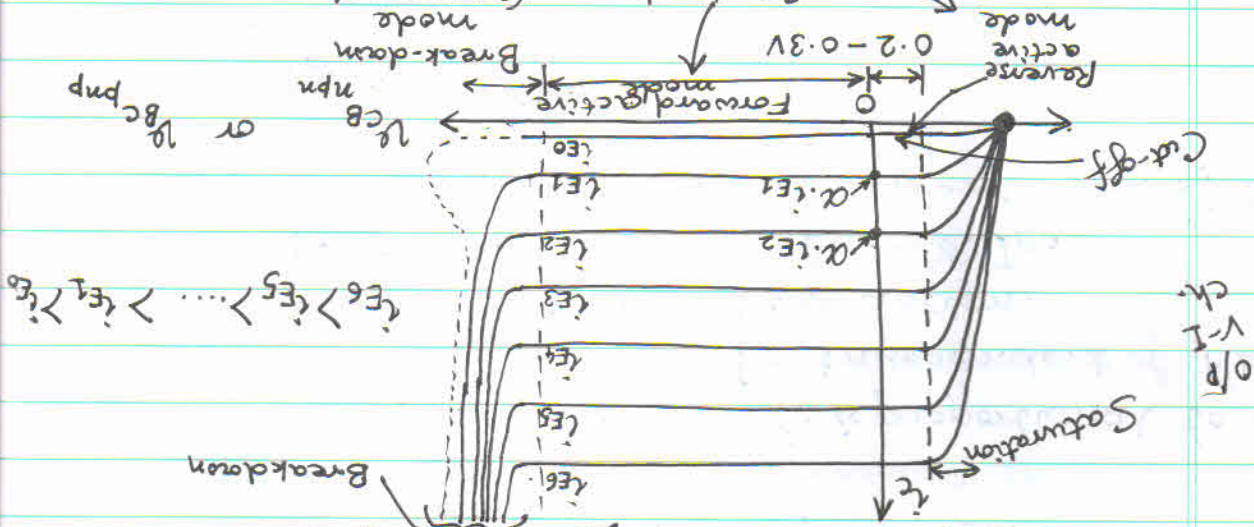
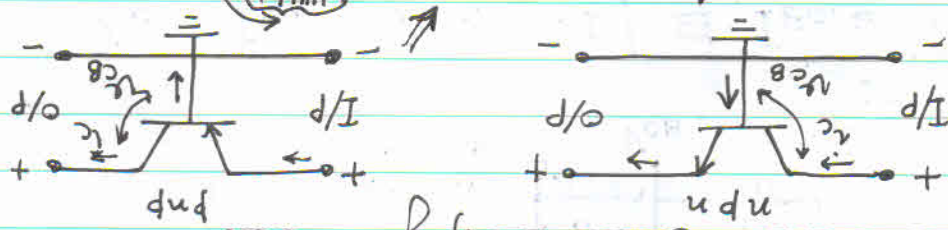
$$\begin{aligned} i_E &= i_c + i_B \\ &= \beta \cdot i_B + i_B \\ &= (1 + \beta) i_B \end{aligned}$$

$$\begin{aligned} i_c &= \left(\frac{\beta}{1 + \beta} \right) i_E \\ &= \alpha \cdot i_E \quad \left(\because \alpha = \frac{\beta}{1 + \beta} \right) \end{aligned}$$

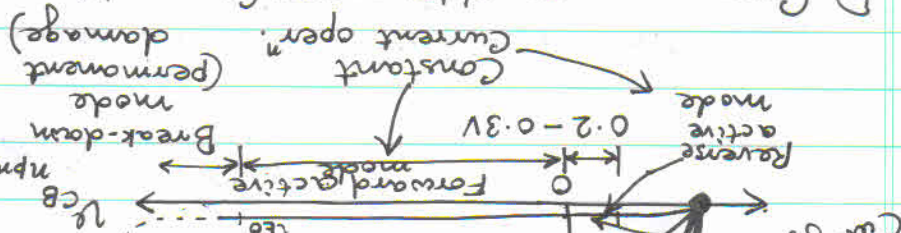
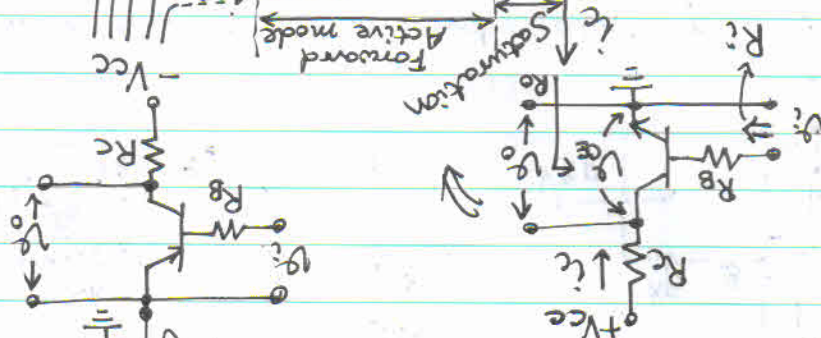
$$\text{or, } \beta = \frac{\alpha}{1-\alpha}$$

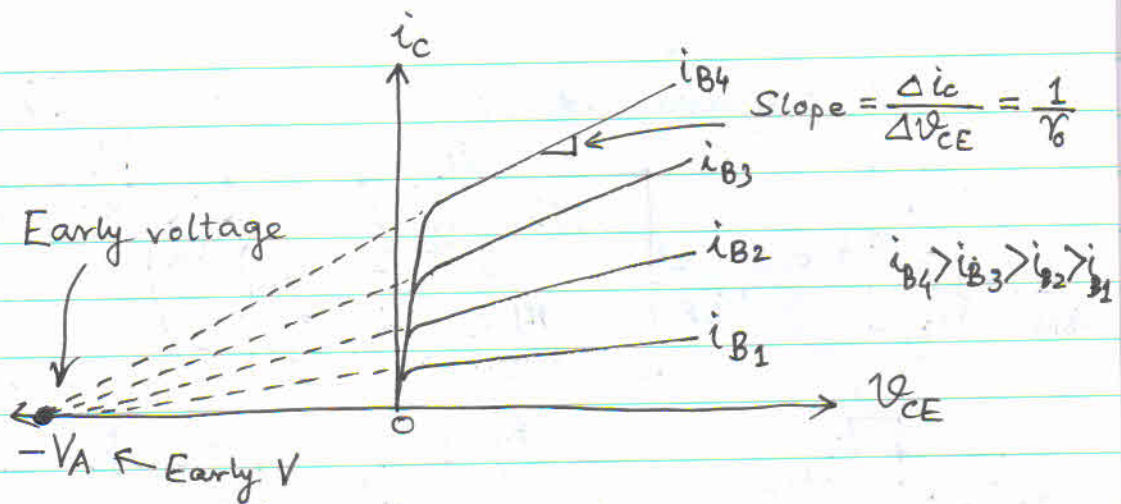
6. V-I characteristics:

a) Common-base configuration:

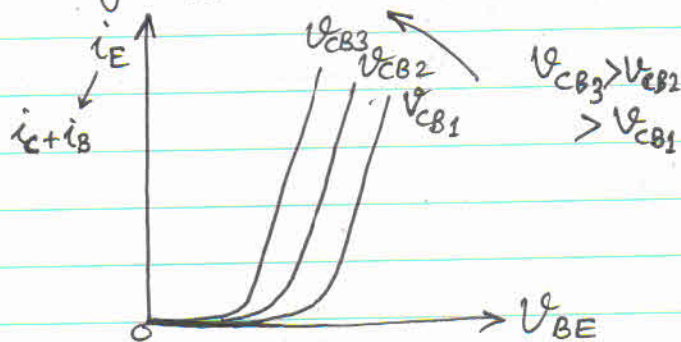


b) Common-emitter configuration:





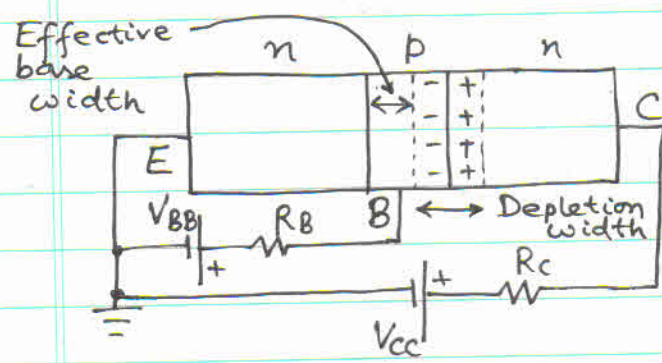
Early effect & base width modulation:



$J_{1CB} : RB$

$J_{2BE} : FB$

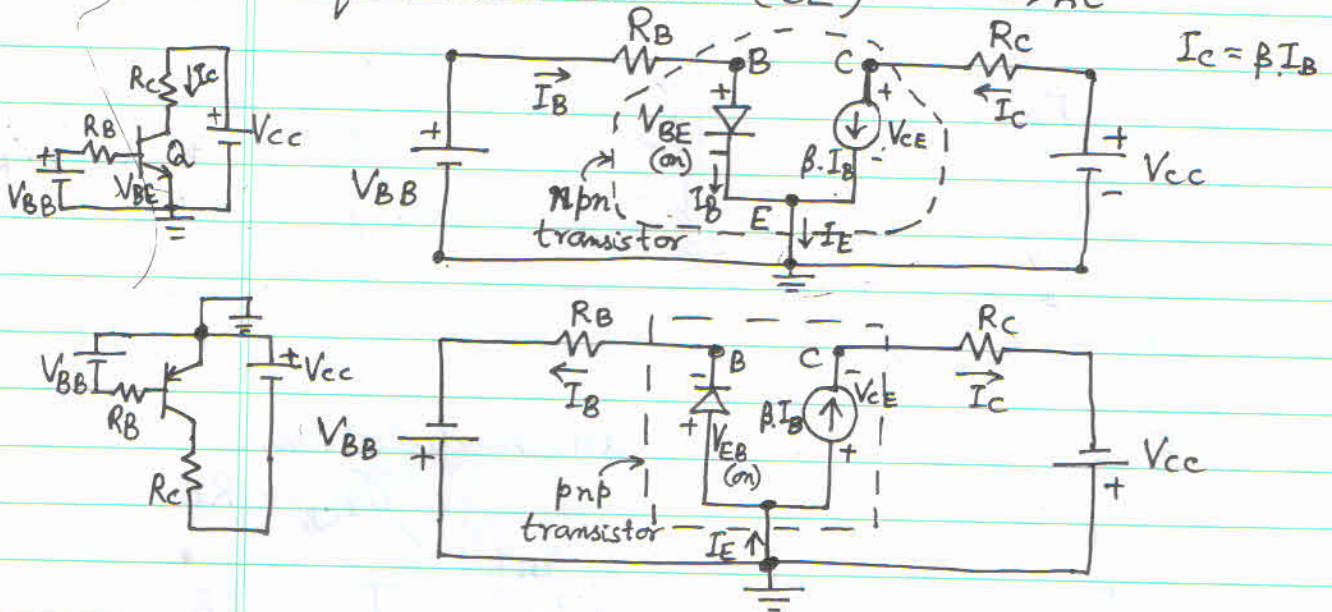
Larger V_{CB} causes wider depletion width, causes reduction in effective base width



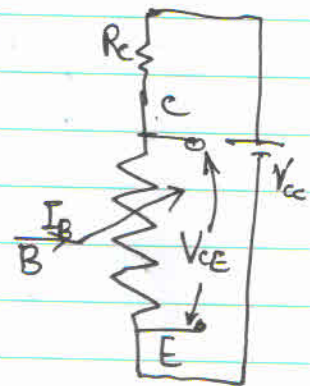
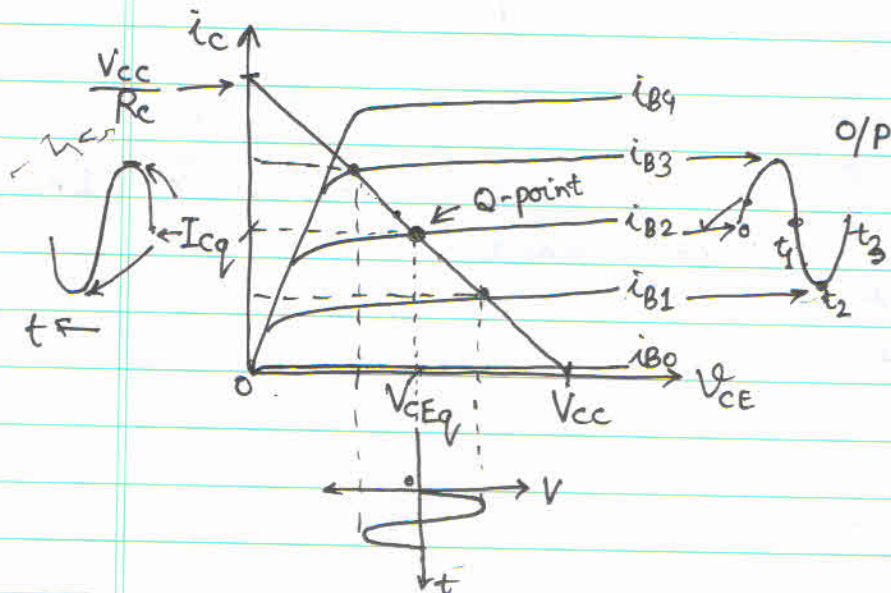
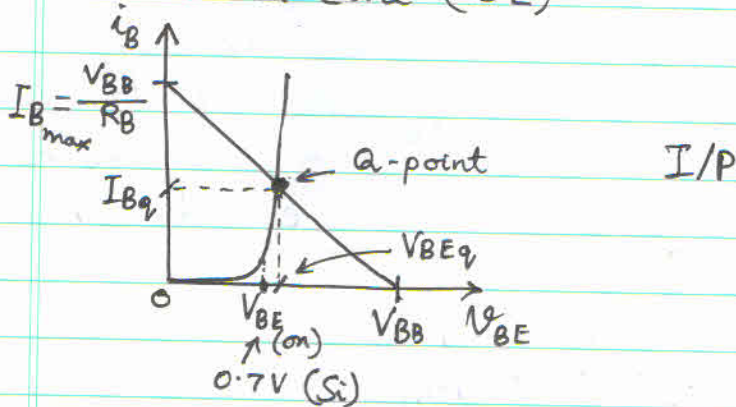
$$\frac{1}{r_o} = \left. \frac{\partial i_c}{\partial V_{CE}} \right|_{V_{BE} = \text{constant}} \quad \left| \quad i_c = I_s \left(e^{\frac{V_{BE}}{V_T}} \right) \left(1 + \frac{V_{CE}}{V_A} \right) \right.$$

$$r_o \approx \frac{V_A}{I_c}$$

7. DC Equivalent circuit (CE):



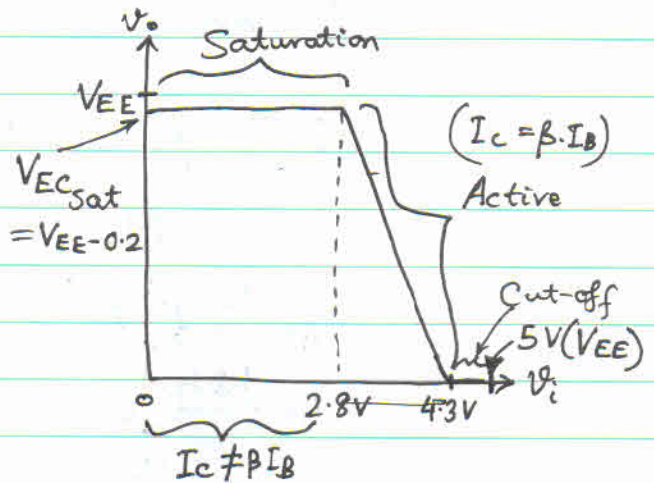
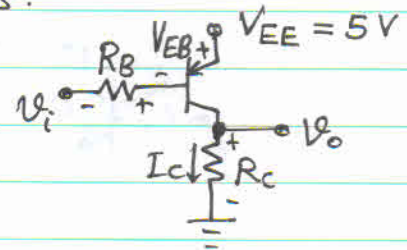
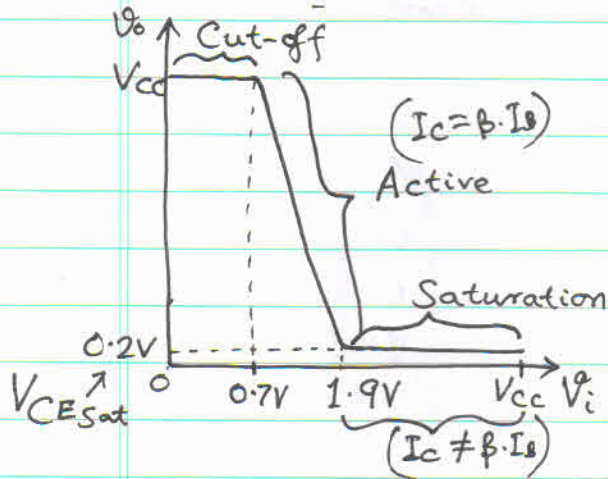
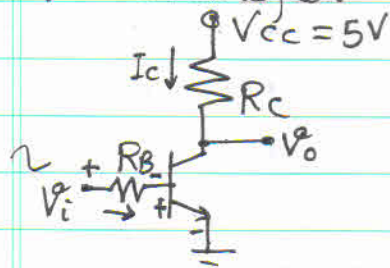
8. DC Load Line (CE)



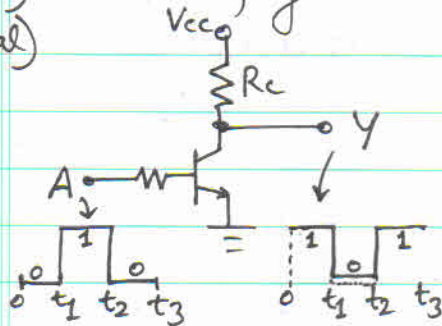
$$I_B = \frac{V_{BB}}{R_B} - \frac{V_{BE}}{R_B} \quad \left| \quad V_{CE} = V_{CC} - I_C \cdot R_C \right.$$

$V_{BE} > V_{CE}$ 2 to 0.3 V

9. V-transfer characteristics:



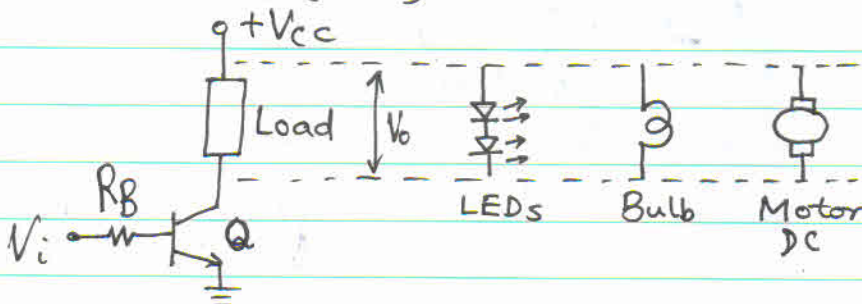
10.a) CE configuration as an inverter (NOT gate)
(Digital)



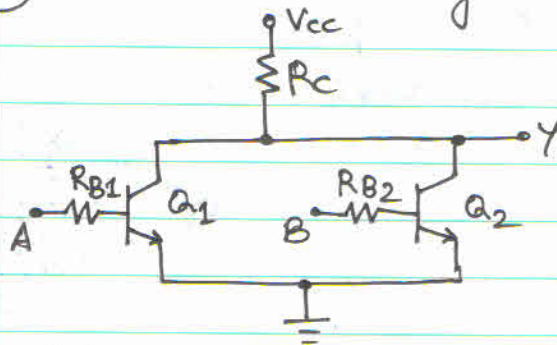
\approx A \rightarrow NOT \rightarrow Y

A	Y
0 (0V)	1 (VCC)
1 (VCC)	0 (0.2V)

b) Transistor (BJT) as a switch:



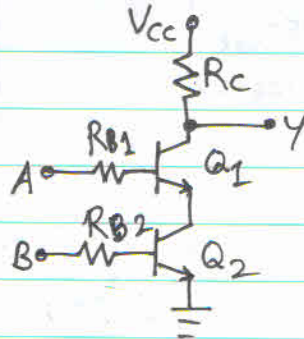
c) BJT as a NOR gate



A	B	Y
0 (0V)	0	1 (V_{cc})
0	1	0
1 (V_{cc})	0	0
1	1	0 (0.2V)

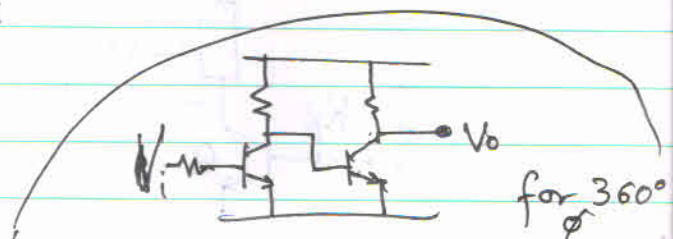
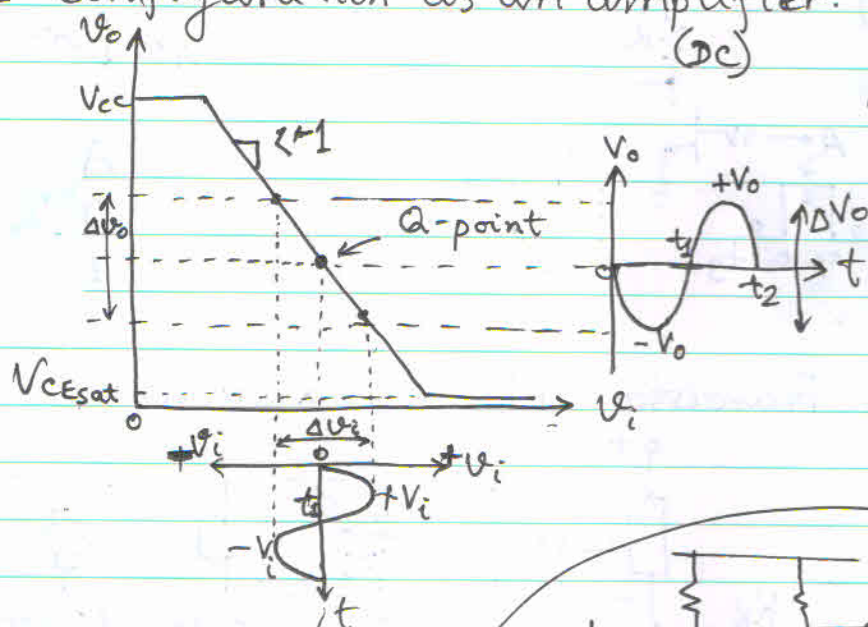
'0' means 0.2V ; '1' means V_{cc} (for O/P Y)

d) BJT as a NAND gate



A	B	Y
0	0	1 $\leftarrow V_{cc}$
0	1	1 $\leftarrow V_{cc}$
1	0	1 $\leftarrow V_{cc}$
1	1	0 $\leftarrow 0.4V$

11. CE configuration as an amplifier: 180° inversion Phase (DC)



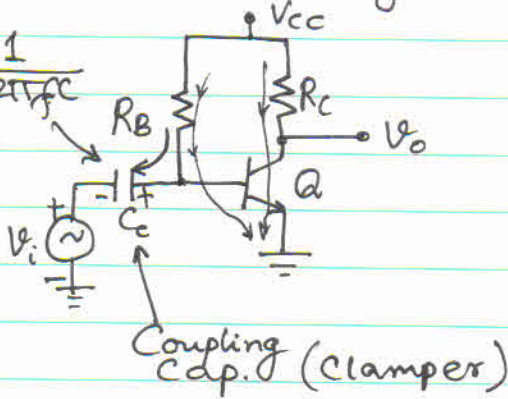
$$I_{Bq} = \frac{V_{CC} - V_{BE(on)}}{R_B} \quad \Bigg| \quad R_C = \frac{V_{CC} - V_{CEq}}{I_{Cq}}$$

$$V_{CEq} = V_{CC} - I_{Cq} R_C \quad \Bigg| \quad I_{Bq} = \frac{I_{Cq}}{\beta}$$

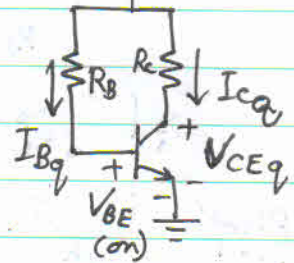
12. BJT Biasing:

a) Fixed R biasing

$$X_C = \frac{1}{2\pi f C}$$

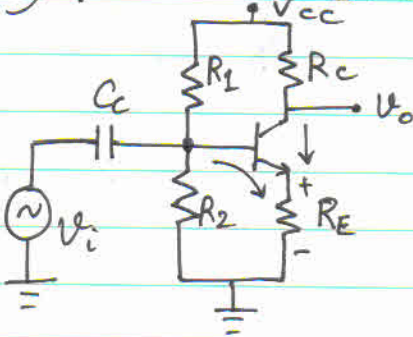


$$R_B = \frac{V_{CC} - V_{BE(on)}}{I_{Bq}}$$

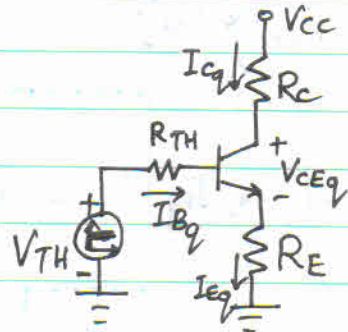


(At DC)

b) V-divider biasing



≈



$$R_{TH} = R_1 // R_2 \quad \Bigg| \quad V_{TH} = \frac{R_2}{R_1 + R_2} \cdot V_{CC}$$

$$I_{Eq} = (1 + \beta) I_{Bq}$$

$$I_{Bq} = \frac{V_{TH} - V_{BE(on)}}{R_{TH} + (1 + \beta) R_E}$$

$$I_{Cq} = \beta \cdot I_{Bq}$$

13. Multi-stage amplifier:

